CDSH270

SILICON SCHOTTKY DIODE

DO-35 CASE

www.centralsemi.com

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CDSH270 silicon Schottky diode is designed to replace the 1N270 Germanium diode. Some advantages over the 1N270 are lower forward voltage, lower leakage current, faster switching speed, and a more robust package.

MARKING: FULL PART NUMBER

MAXIMUM RATINGS: (T_A=25°C)	**SYMBOL**		**UNITS**
Peak Repetitive Reverse Voltage	V_{RRM}	100	V
Continuous Forward Current	I_F	100	mA
Peak Repetitive Forward Current	I_{FRM}	350	mA
Peak Forward Surge Current, tp=10ms	I_{FSM}	750	mA
Power Dissipation	P_D	100	mW
Operating Junction Temperature	T_J	-65 to +125	°C
Storage Temperature	T_{stg}	-65 to +150	°C
Thermal Resistance	Θ_{JA}	300	°C/W

ELECTRICAL CHARACTERISTICS: (T_A=25°C unless otherwise noted)

SYMBOL	**TEST CONDITIONS**	**TYP**	**MAX**	**UNITS**
I_R	V_R=50V		100	nA
I_R	V_R=50V, T_A=100°C		20	μA
V_F	I_F=1.0mA		0.45	V
V_F	I_F=100mA	0.9		V
V_F	I_F=200mA		1.0	V
C_J	V_R=10V, f=1.0MHz	1.2		pF

R1 (16-August 2012)

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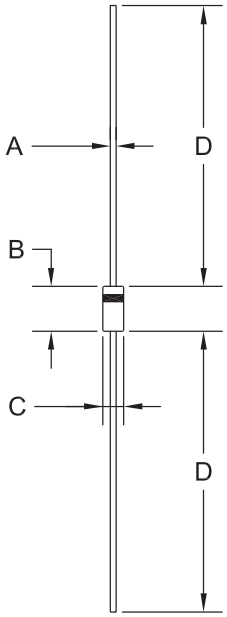
DO-35 CASE - MECHANICAL OUTLINE



R1

DIMENSIONS				
	INCHES		MILLIMETERS	
SYMBOL	MIN	MAX	MIN	MAX
A	0.018	0.022	0.46	0.56
B	0.120	0.200	3.05	5.08
C	0.060	0.090	1.52	2.29
D	1.000	-	25.40	-

DO-35 (REV: R1)

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